



PJQ4441P

40V P-Channel Enhancement Mode MOSFET

Voltage

-40 V

Current

-44 A

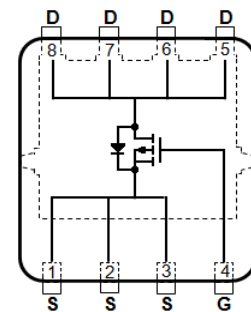
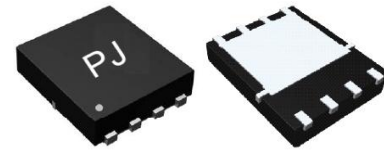
Features

- $R_{DS(ON)}$, $V_{GS}@-10V$, $I_D@-10A < 17m\Omega$
- $R_{DS(ON)}$, $V_{GS}@-4.5V$, $I_D@-8A < 25m\Omega$
- Advanced Trench Process Technology
- High density cell design for ultralow on-resistance
- Lead free in compliance with EU RoHS 2.0
- Green molding compound as per IEC 61249 standard

Mechanical Data

- Case : DFN3333-8L Package
- Terminals : Solderable per MIL-STD-750, Method 2026
- Approx. Weight : 0.001 ounces, 0.03 grams

DFN3333-8L



Maximum Ratings and Thermal Characteristics ($T_A=25^\circ C$ unless otherwise noted)

PARAMETER		SYMBOL	LIMIT	UNITS
Drain-Source Voltage		V_{DS}	-40	V
Gate-Source Voltage		V_{GS}	± 20	
Continuous Drain Current (Note 4)	$T_C=25^\circ C$	I_D	-44	A
	$T_C=100^\circ C$		-28	
Pulsed Drain Current (Note 1)	$T_C=25^\circ C$	I_{DM}	-135	
Power Dissipation	$T_C=25^\circ C$	P_D	59.5	W
	$T_C=100^\circ C$		24	
Continuous Drain Current (Note 4)	$T_A=25^\circ C$	I_D	-8.5	A
	$T_A=70^\circ C$		-7	
Power Dissipation	$T_A=25^\circ C$	P_D	2	W
	$T_A=70^\circ C$		1.3	
Operating Junction and Storage Temperature Range		T_J, T_{STG}	-55~150	$^\circ C$
Typical Thermal Resistance (Note 4,5)	Junction to Case	$R_{\theta JC}$	2.1	$^\circ C/W$
	Junction to Ambient	$R_{\theta JA}$	59.5	

- Limited only By Maximum Junction Temperature



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Electrical Characteristics ($T_A=25^\circ\text{C}$ unless otherwise noted)

PARAMETER	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNITS
Static						
Drain-Source Breakdown Voltage	BV_{DSS}	$V_{GS}=0V, I_D=-250\mu A$	-40	-	-	V
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS}=V_{GS}, I_D=-250\mu A$	-1	-1.6	-2.5	
Drain-Source On-State Resistance	$R_{DS(on)}$	$V_{GS}=-10V, I_D=-10A$	-	14	17	m Ω
		$V_{GS}=-4.5V, I_D=-8A$	-	20	25	
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS}=-40V, V_{GS}=0V$	-	-	-1	μA
Gate-Source Leakage Current	I_{GSS}	$V_{GS}=\pm 20V, V_{DS}=0V$	-	-	± 100	nA
Dynamic (Note 6)						
Total Gate Charge	Q_g	$V_{DS}=-32V, I_D=-10A,$ $V_{GS}=-4.5V$ (Note 1,2)	-	19	-	nC
Gate-Source Charge	Q_{gs}		-	5.3	-	
Gate-Drain Charge	Q_{gd}		-	6.6	-	
Input Capacitance	C_{iss}	$V_{DS}=-25V, V_{GS}=0V,$ $f=1\text{MHZ}$	-	2030	-	pF
Output Capacitance	C_{oss}		-	190	-	
Reverse Transfer Capacitance	C_{rss}		-	139	-	
Turn-On Delay Time	$t_{d(on)}$	$V_{DS}=-20V, I_D=-1A,$ $V_{GS}=-10V, R_G=6\Omega$ (Note 1,2)	-	8.6	-	ns
Turn-On Rise Time	t_r		-	9.6	-	
Turn-Off Delay Time	$t_{d(off)}$		-	77	-	
Turn-Off Fall Time	t_f		-	39	-	
Drain-Source Diode						
Maximum Continuous Drain-Source Diode Forward Current	I_S	---	-	-	-44	A
Diode Forward Voltage	V_{SD}	$I_S=-1A, V_{GS}=0V$	-	-0.7	-1	V

NOTES :

1. Pulse width $\leq 300\mu s$, Duty cycle $\leq 2\%$.
2. Essentially independent of operating temperature typical characteristics.
3. Repetitive rating, pulse width limited by junction temperature $T_{J(MAX)}=150^\circ\text{C}$. Ratings are based on low frequency and duty cycles to keep initial $T_J=25^\circ\text{C}$.
4. The maximum current rating is package limited.
5. $R_{\theta JA}$ is the sum of the junction-to-case and case-to-ambient thermal resistance where the case thermal reference is defined as the solder mounting surface of the drain pins. Mounted on a 1 inch² with 2oz.square pad of copper.
6. Guaranteed by design, not subject to production testing.



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TYPICAL CHARACTERISTIC CURVES

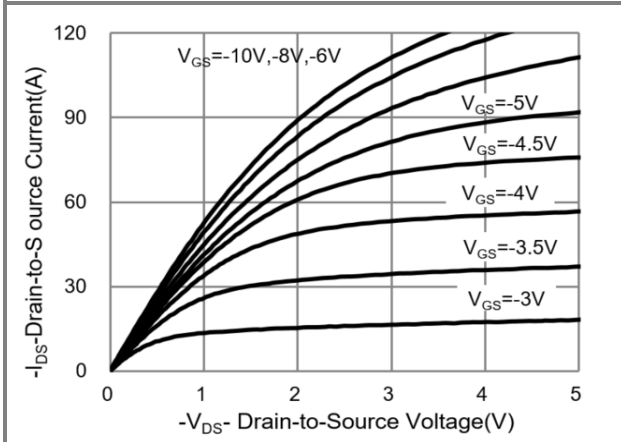


Fig.1 On-Region Characteristics

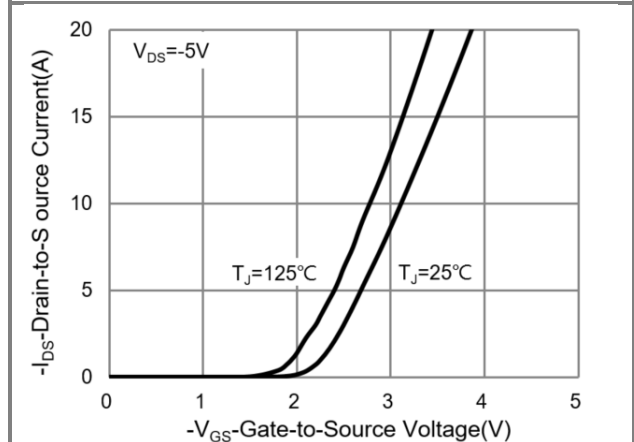


Fig.2 Transfer Characteristics

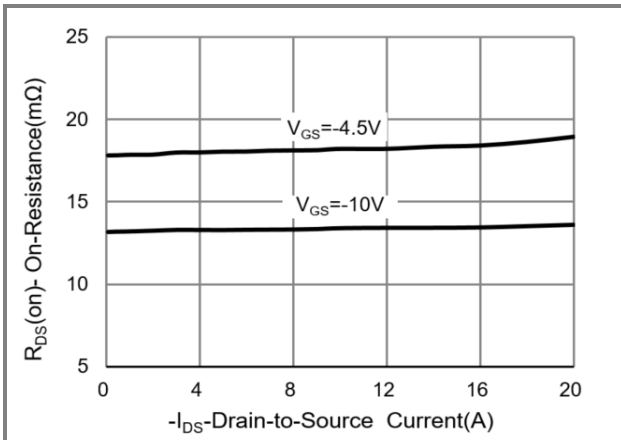


Fig.3 On-Resistance vs. Drain Current

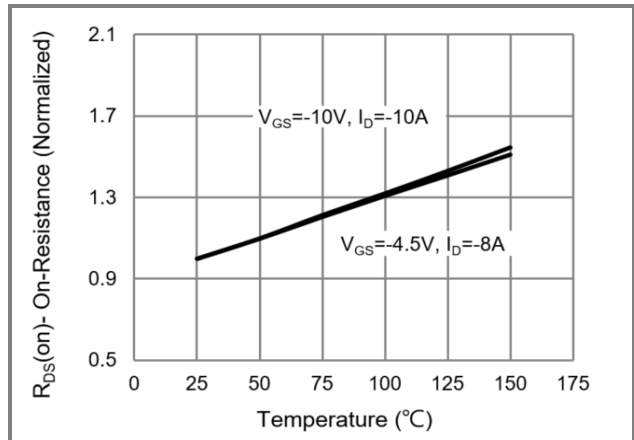


Fig.4 On-Resistance vs. Junction temperature

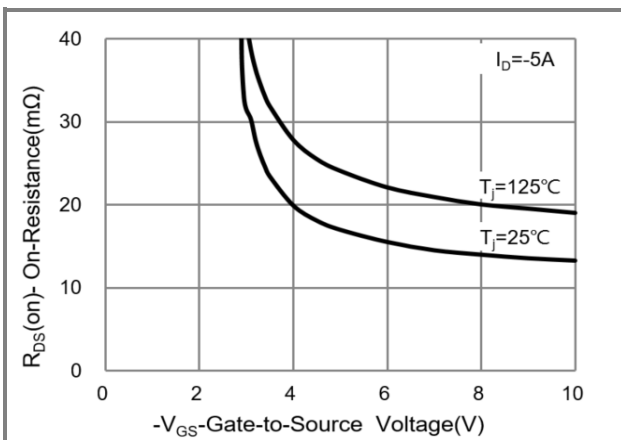


Fig.5 On-Resistance Variation with V_{GS}

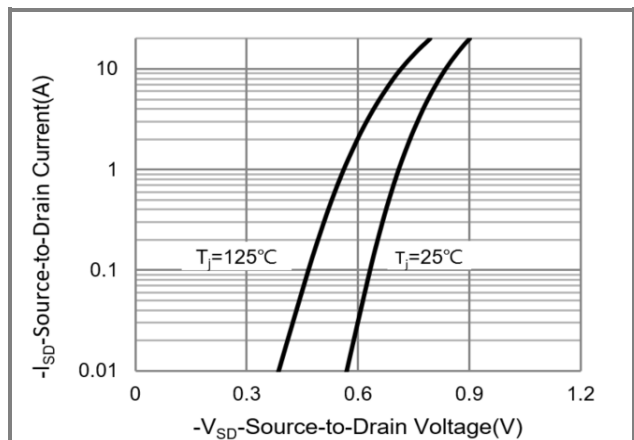


Fig.6 Source-Drain Diode Forward Voltage



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TYPICAL CHARACTERISTIC CURVES

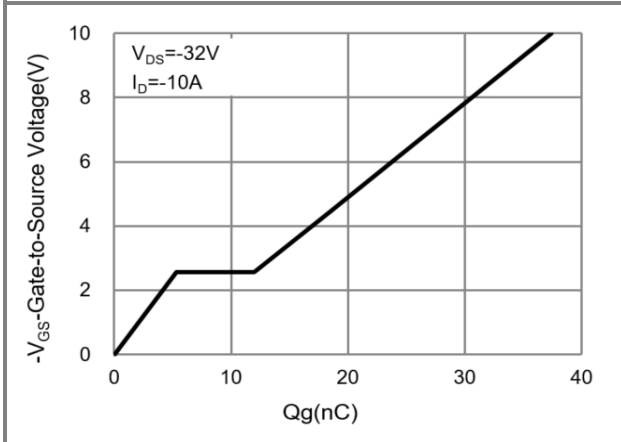


Fig.7 Gate-Charge Characteristics

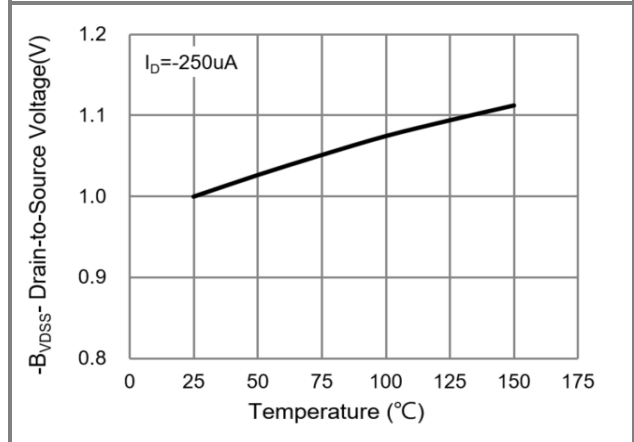


Fig.8 Breakdown Voltage Variation vs. Temperature

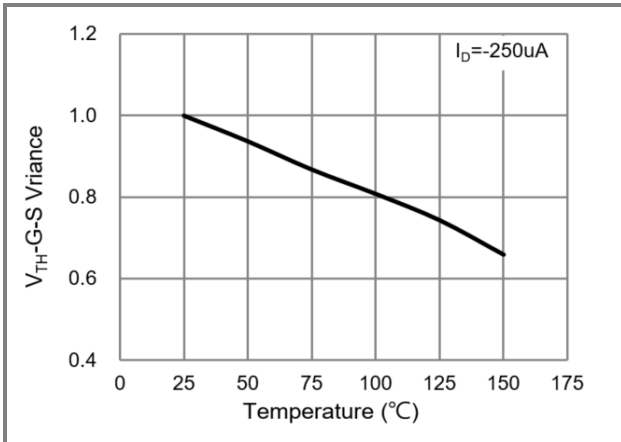


Fig.9 Threshold Voltage Variation with Temperature

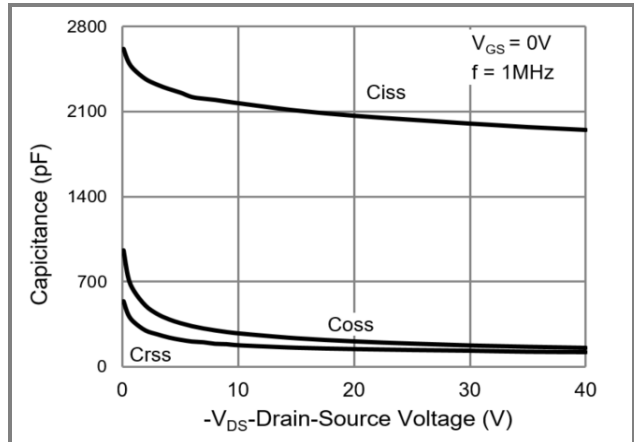


Fig.10 Capacitance vs. Drain-Source Voltage

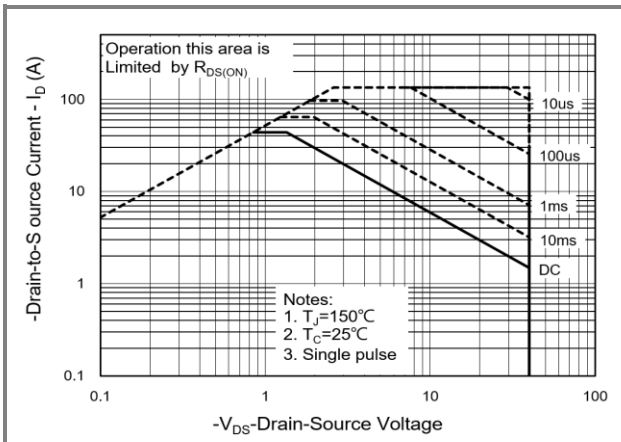


Fig.11 Maximum Safe Operating Area

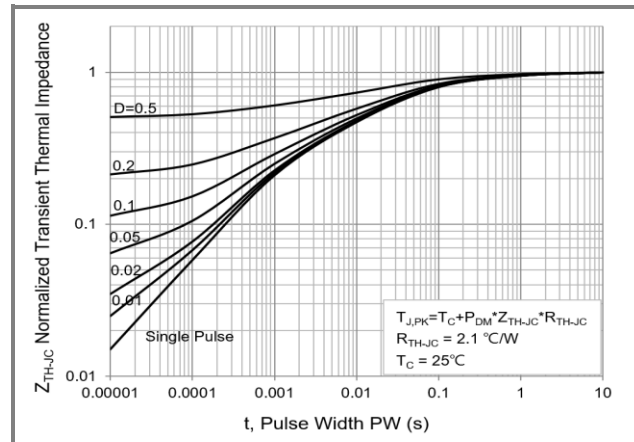


Fig.12 Normalized Transient Thermal Impedance



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